

ML8511A

UV Sensor with Voltage Output

GENERAL DESCRIPTION

The ML8511A is a UV sensor, which is suitable for acquiring UV intensity indoors or outdoors. The ML8511A is equipped with an internal amplifier, which converts photo-current to voltage depending on the UV intensity. This unique feature offers an easy interface to external circuits such as ADC. In the power down mode, typical standby current is 0.1μ A, thus enabling a longer battery life.

FEATURES

- Photodiode sensitive to UV-A and UV-B
- Embedded operational amplifier
- Analog voltage output
- Low supply current (300µA typ.) and low standby current (0.1µA typ.)
- Small and thin surface mount package (4.0mm x 3.7mm x 0.73mm, 12-pin ceramic QFN)

APPLICATIONS

• Smart phone, Smart watch, Wealable helthcare device, Weather station, Bicycle navigation, Accessary

BLOCK DIAGRAM



PIN CONFIGURATIONS

Pin	Symbol	I/O	Function	
7	VDD	PW	Supply voltage. Decouple this pin to ground with 0.1 μ F capacitor.	
5	GND	PW	Ground	
4	EN	I	Active high enable pin. (High: Active mode, Low: Standby mode)	
8	OUT	0	Output (Low in power down or standby mode)	
10	TR	I/O	Internal reference voltage. Decouple this pin to ground with 1 nF capacitor.	
1,2,3,6,9,11,12	NC	-	No Connection. Do not connect.	



FEDL8511A-02

Issue Date: October 6, 2015

EXAMPLE OF CONNECTING DIAGRAM



* Load resistance of OUT port is recommended more than 100 k $\Omega.$

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Rating	unit
Supply Voltage	V _{DD}	Ta=25 °C	-0.3 to +4.6	V
Input Voltage	VI	Ta=25 °C	-0.3 to +4.6	V
Output Short Current	l _{os}	Ta=25 °C	5	mA
Power Dissipation	PD	Ta=25 °C	30	mW
Storage Temperature	T _{stg}	-	-30 to +85	°C

RECOMMENDED OPERATION CONDITIONS

Parameter	Symbol	Min.	Тур.	Max.	unit
Operating Voltage	V _{DD}	2.7	3.3	3.6	V
Operating Temperature	Та	-20	-	70	°C

ELECTRO-OPTICAL CHARACTERISTICS

(V_{DD})	=+2.7V to	+3.6V	$Ta = -20^{\circ}C$	$t_0 + 70^{\circ}C$
	$-\tau_2.7 \times 10$	- ± J.U V	1a - 20 C	10 ± 10 C)

			(, DD=,	2.7 1 10 13.0	v, 1a20 C	
Parameter	Symbol	Condition	Min.	Тур.	Max.	unit
Supply Current (active mode)	I _{DDA}	V _{EN} =V _{DD}	-	300	500	μA
Supply Current (standby mode)	I _{DDS}	V _{EN} =0	-	0.1	1	μA
Input Voltage (High level)	V _{IH}	-	$V_{DD} \times 0.8$	-	$V_{\text{DD}} + 0.3$	V
Input Voltage (Low level)	V_{IL}	-	-0.2	-	0.72	V
High level input current	I _{IH}	V _{EN} =V _{DD}	-	-	1	μA
Low level input current	IIL	V _{EN} =0	-1	-	-	μA
Wavelength of maximum sensitivity	λр	Ta=25°C	-	365	-	nm
Output Setup Time	Τ _{SU}	V _{EN} =V _{DD}	-	-	1	ms
Output Voltage (Shading) *	V_{REF}	Ta=25°C, V _{EN} =V _{DD}	0.95	1.0	1.05	V
Output Voltage (10mW/cm ² at λp) *	Vo	Ta=25°C, V _{EN} =V _{DD}	2.08	2.2	2.32	V

* Load resistance of OUT port is recommended more than 100 k $\Omega.$



OUTPUT VOLTAGE- UV INTENSITY CHARACTERISTICS

SPECTRAL RESPONSIBILITY CHARACTERISTICS



TIMING CHART

Supply voltage and EN signal state should take one of the following procedures:

- 1. EN should be HIGH or LOW at the same time when V_{DD} is applied.
- 2. EN should be HIGH or LOW while V_{DD} is applied.

Output should be read after output voltage level becomes stable. Maximum time required until stable output voltage reaches is 1 millisecond after EN goes HIGH.



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PACKAGE DIMENSIONS



Cautions

Do not touch the surface of the resin covering the top of the package as the resin is scrached easily and bonding wires under the resign may be dameged.

Specifications are defined without considering the UV absorption by an external cover material. If a cover is used over the sensor, take the UV transparancy of the cover into consideration.

LAPIS Semiconductor Co., Ltd.

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REVISION HISTORY

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Document No.	Date	Previous Edition	Current Edition	Description	
FEDL8511A-01	April. 1, 2015	-		Initial release	
FEDL8511A-02	October 6, 2015	1	1	Block diagram and pin configurations are modified with removal of internal bonding wires.	
		6	6	Added "Top view" and "Bottom view".	

Notes

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